NSN 5961-00-831-2884

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Inclosure Material:

Metal

Overall Length:

0.375 inches

Overall Diameter:

0.875 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

60.0 breakdown voltage, collector-to-base, emitter open and 45.0 breakdown voltage, collector-to-emitter, base open and 9.0 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

Between 1.30 amperes source cutoff current and 4.00 amperes source cutoff current

Power Rating Per Characteristic:

50.0 watts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Max sat. Resistance 2.0 ohms; junction pattern arrangement: npn

Terminal Type And Quantity:

2 uninsulated wire lead and 1 case

Specification Data:

80131-release2402 professional/industrial association specification

Specification Or Standard:

2n1069 type

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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